

ABSTRACT OF THE DISCLOSURE

A depletion enhancement layer having a striped opening on the upper surface of a ridge portion, a low carrier concentration layer and an n-type current blocking layer are successively formed on a p-type cladding layer having the ridge portion. The low carrier concentration layer has a lower carrier concentration than the n-type current blocking layer. The band gap of the depletion enhancement layer is set to an intermediate level between the band gaps of the p-type cladding layer and the low carrier concentration layer. Alternatively, a first current blocking layer having a low carrier concentration and a second current blocking layer of the opposite conduction type are formed on an n-type depletion enhancement layer, and a p-type contact layer is formed on the second current blocking layer of the opposite conduction type and another p-type contact layer.